

AMENDMENTS TO THE CLAIMS

Please amend the claims as follows:

1. (Withdrawn) A unit-layer post-treatment catalyst chemical-vapor-deposition apparatus for forming a thin film on a substrate by using the catalyst action of an exothermic catalyst body resistance-heated in a reactive vessel capable of performing vacuum pumping, comprising: a gas supply system capable of introducing flow rates of thin-film-component-contained gas and hydrogen gas into the reactive vessel like a pulse; and an exhaust system capable of performing vacuum pumping and pressure control, wherein the above thin-film-component-contained gas and hydrogen gas introduced like a pulse contact with the exothermic catalyst body and decompose and form a thin film for each unit layer on the substrate, and form a laminated thin film by surface-treating the thin film for each unit layer.
2. (Withdrawn) The unit-layer post-treatment catalyst chemical-vapor-deposition apparatus according to claim 1, characterized in that the surface treatment is one or both of the surface treatment by thin-film-component-contained gas excluding silicon and containing active species and the surface treatment by hydrogen gas containing active species.
3. (Withdrawn) The unit-layer post-treatment catalyst chemical-vapor-deposition apparatus according to claim 1, characterized in that the catalyst performance is regenerated by applying hydrogen gas to the exothermic catalyst body.

4. (Withdrawn) The unit-layer post-treatment catalyst chemical-vapor-deposition apparatus according to claim 1, characterized in that the surface treatment is one or both of the extracting treatment of surplus thin-film component and direct adding treatment of a thin-film component.
5. (Withdrawn) The unit-layer post-treatment catalyst chemical-vapor-deposition apparatus according to claim 1, characterized in that one of nitrogen gas and rare gas is used instead of the hydrogen gas.
6. (Withdrawn) The unit-layer post-treatment catalyst chemical-vapor-deposition apparatus according to claim 1, characterized in that the thin-film-component-contained gas is made of at least one of hydride of silicon and halide of silicon, and at least one of nitrogen and hydride of nitrogen.
7. (Withdrawn) The unit-layer post-treatment catalyst chemical-vapor-deposition apparatus according to claim 1, characterized in that the thin-film-component-contained gas containing active species in the surface treatment is one or both of nitrogen and hydride of nitrogen.
8. (Currently Amended) A method for forming a laminated thin SiN film on a substrate composed of plural unit layers, each unit layer comprising a surface-treated

thin film using an exothermic catalyst body resistance heated in a reaction vessel, said method comprising:

an activating step of generating active species by bringing a thin-film-component gas containing silicon, a gas containing a nitrogen component, and a hydrogen gas into contact with the exothermic catalyst body, thereby generating active species of the gases;

a film forming step of forming a thin SiN film for each unit layer on a substrate;

a surface treating step of surface-treating the thin film for each unit layer by the hydrogen gas active species;

another surface treating step of surface-treating the thin film for each unit layer by the active species of the gas containing the nitrogen component; and

repeating one of the one surface treating step and the other surface treating step for each unit layer,

wherein the surface treating step and the other surface treating step can be carried out in any order,

wherein the last step of the final repetition of said repeating is the other surface treating step, and

whereby a laminated thin film is formed by the unit layers.

9. (Previously Presented) The method according to claim 8, further comprising a step of repeating one of the one surface treating step and other surface treating step a plurality of times for each unit layer.

10. (Previously Presented) The method according to claim 8, wherein said film forming step and one or both of said one surface treating step and said other surface treating step are performed continuously.
11. (Previously Presented) The method according to claim 8, further comprising the step of vacuum-pumping remaining gas after one of the film forming step, the one surface treating step and the other surface treating step.
12. (Previously Presented) The method according to claim 8, wherein the one surface treating step is extracting a surplus thin-film component and the other surface treating step is adding a thin-film component.
13. (Previously Presented) The method according to claim 8, wherein the final step for a specific unit layer is performing surface treatment by thin-film-component gas active species excluding silicon.
14. (Previously Presented) The method according to claim 8, wherein one of nitrogen gas and an inert gas is used in addition to hydrogen gas.
15. (Previously Presented) The method according to claim 8, wherein the thin-film-component gas is made of at least one of a hydride of silicon and a halide of silicon, and at least one of nitrogen and a hydride of nitrogen.

16. (Previously Presented) The method according to claim 8, wherein the active species in the surface treatment is one or both of nitrogen and a hydride of nitrogen.

17. (Previously Presented) The method according to claim 8, wherein the thin-film-component gas is made of a monosilane gas and ammonia gas, the film forming step forms a silicon nitride film for each unit layer on a substrate, and the other surface treating step is surface-treating a silicon nitride film for each unit layer by ammonia gas active species.

18. (Previously Presented) The method according to any one of claims 15 to 17, wherein a final step of forming a specific unit layer comprises performing surface treatment by ammonia gas active species.

19. (Cancelled)